Unit: mm

TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD1412A

High-Current Switching Applications
Power Amplifier Applications

• Low saturation voltage: V_{CE} (sat) = 0.4 V (max) at I_{C} = 4 A

Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	70	V	
Collector-emitter voltage		V _{CEO}	50	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		Ic	7	Α	
Base current		Ι _Β	1	Α	
Collector power dissipation	Ta = 25°C	Pc	2.0	W	
	Tc = 25°C	FC	30		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

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Weight: 1.7 g (typ.)

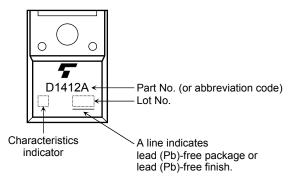
operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Tc = 25°C)

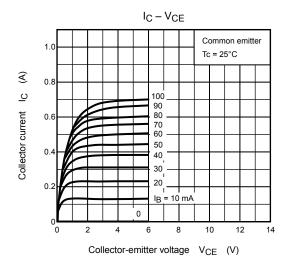
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I _{CBO}	V _{CB} = 70 V, I _E = 0	_	_	30	μA
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	50	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	50	_	_	V
DC current gain		h _{FE (1)} (Note)	V _{CE} = 1 V, I _C = 1 A	70	_	240	
		h _{FE (2)}	V _{CE} = 1 V, I _C = 4 A	30	_	_	
Collector-emitter	saturation voltage	V _{CE} (sat)	I _C = 4 A, I _B = 0.4 A	_	0.2	0.4	V
Base-emitter satu	uration voltage	V _{BE} (sat)	I _C = 4 A, I _B = 0.4 A	_	0.9	1.2	V
Transition freque	ncy	f _T	V _{CE} = 4 A, I _C = 1 A	_	10	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	250	_	pF
Switching time Stora	Turn-on time	t _{on}	20 μs Input $\stackrel{\text{IB1}}{\longrightarrow}$ Output $\stackrel{\text{Output}}{\longrightarrow}$ $\stackrel{\text{Output}$	_	0.2	_	
	Storage time	t _{stg}		_	2.5	_	μs
	Fall time	t _f			0.5	_	

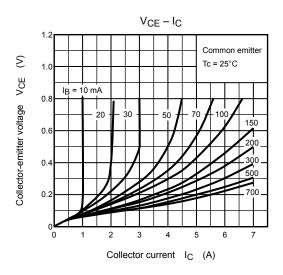
Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240

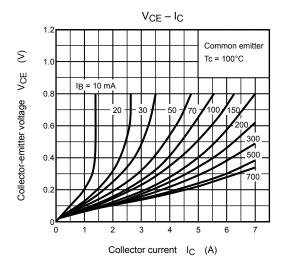
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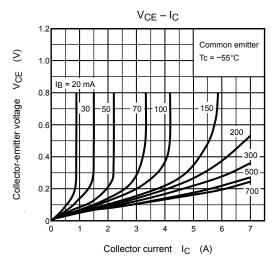


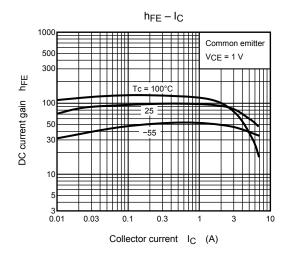
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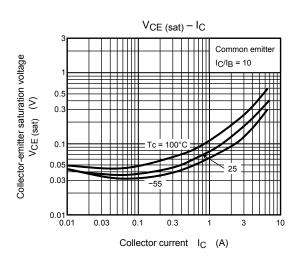




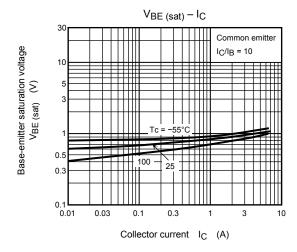


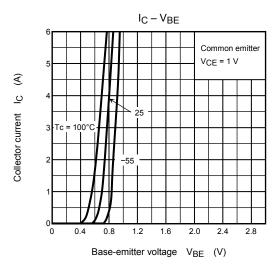


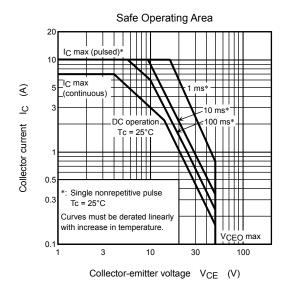




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